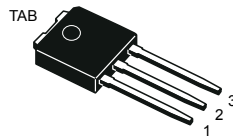
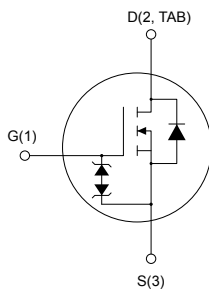


## N-channel 650 V, 1.4 $\Omega$ typ., 3.5 A MDmesh M6 Power MOSFET in an IPAK package


**IPAK**


AM01476v1\_tab


**Product status link**
[STU3N65M6](#)
**Product summary**

<b>Order code</b>	STU3N65M6
<b>Marking</b>	3N65M6
<b>Package</b>	IPAK
<b>Packing</b>	Tube

### Features

Order code	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$
STU3N65M6	650 V	1.5 $\Omega$	3.5 A

- Reduced switching losses
- Lower  $R_{DS(on)}$  per area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

The new MDmesh M6 technology incorporates the most recent advancements to the well-known and consolidated MDmesh family of SJ MOSFETs. STMicroelectronics builds on the previous generation of MDmesh devices through its new M6 technology, which combines excellent  $R_{DS(on)}$  per area improvement with one of the most effective switching behaviors available, as well as a user-friendly experience for maximum end-application efficiency.

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	3.5	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	2.2	A
$I_{DM}^{(1)}$	Drain current (pulsed)	14	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	45	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	5	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	100	
$T_J$	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		

1. Pulse width limited by safe operating area
2.  $I_{SD} \leq 3.5\text{ A}$ ,  $di/dt=400\text{ A}/\mu\text{s}$ ;  $V_{DS(peak)} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$
3.  $V_{DS} \leq 520\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance, junction-to-case	2.78	$^\circ\text{C}/\text{W}$
$R_{thJA}$	Thermal resistance, junction-to-ambient	100	

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	1	A
$E_{as}$	Single pulse avalanche energy (starting $T_J=25\text{ }^\circ\text{C}$ , $I_D=I_{AR}$ , $V_{DD}=50\text{ V}$ )	78	mJ

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 4. On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	650			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ °C}$ <sup>(1)</sup>			100	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 5$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2.25	3	3.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 1.75\text{ A}$		1.4	1.5	$\Omega$

1. Specified by design, not tested in production.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	150	-	$\text{pF}$
$C_{oss}$	Output capacitance		-	13	-	
$C_{rss}$	Reverse transfer capacitance		-	0.7	-	
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}$ , $V_{GS} = 0\text{ V}$	-	31	-	$\text{pF}$
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	5.2	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 3.5\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ , (see Figure 14. Test circuit for gate charge behavior)	-	6	-	$\text{nC}$
$Q_{gs}$	Gate-source charge		-	1	-	
$Q_{gd}$	Gate-drain charge		-	3.2	-	

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$ , $I_D = 1.75\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	5.2	-	$\text{ns}$
$t_r$	Rise time		-	5.4	-	
$t_{d(off)}$	Turn-off delay time		-	14.1	-	
$t_f$	Fall time		-	17.1	-	

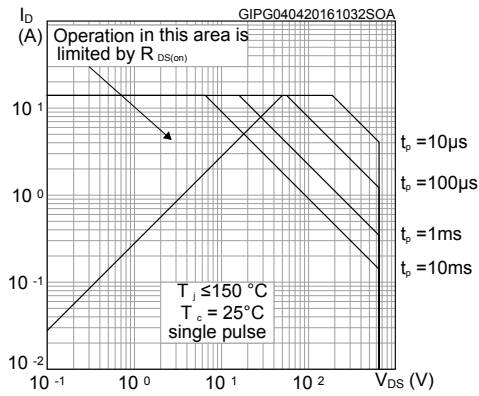
**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		3.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		14	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 3.5 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, V_{DD} = 60 \text{ V}$ , (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	159		ns
$Q_{rr}$	Reverse recovery charge		-	0.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	8.9		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 3.5 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	190		ns
$Q_{rr}$	Reverse recovery charge		-	0.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	8.5		A

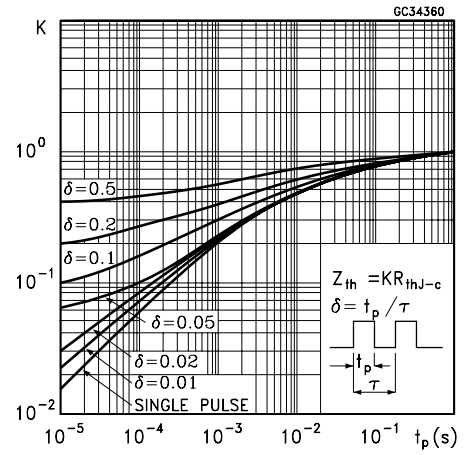
1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

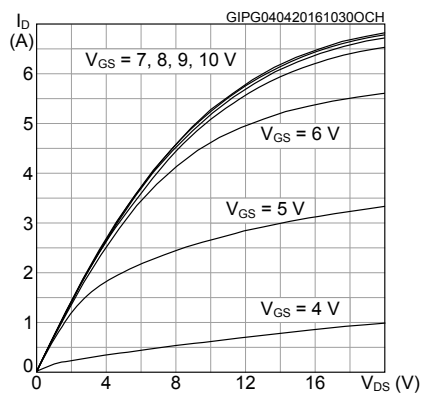
**Figure 1. Safe operating area**



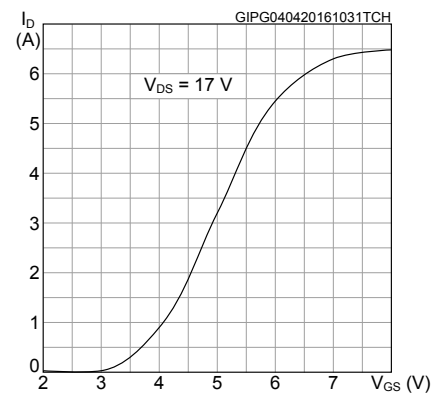
**Figure 2. Thermal impedance**



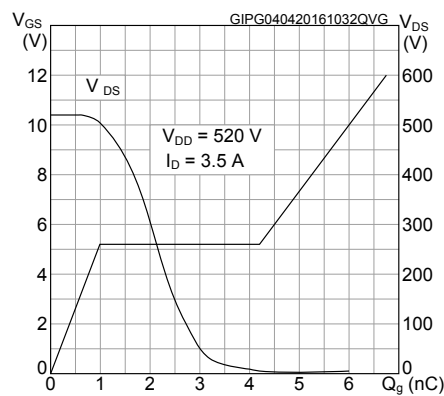
**Figure 3. Output characteristics**



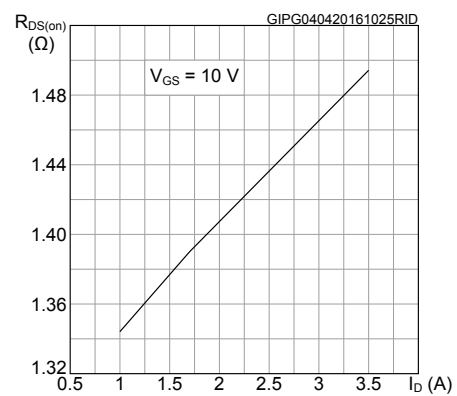
**Figure 4. Transfer characteristics**



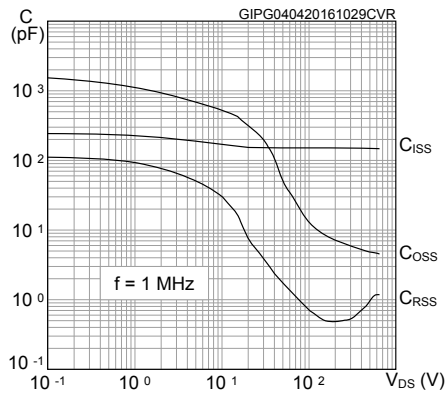
**Figure 5. Gate charge vs gate-source voltage**



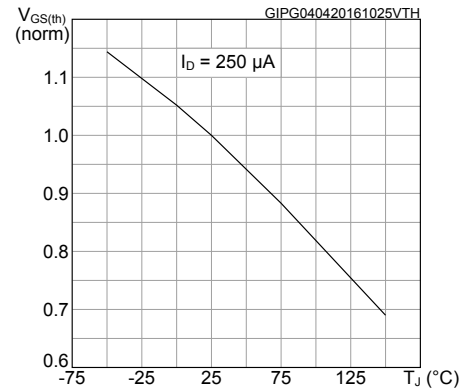
**Figure 6. Static drain-source on-resistance**



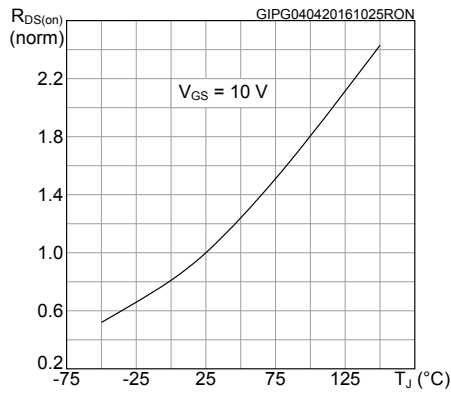
**Figure 7. Capacitance variations**



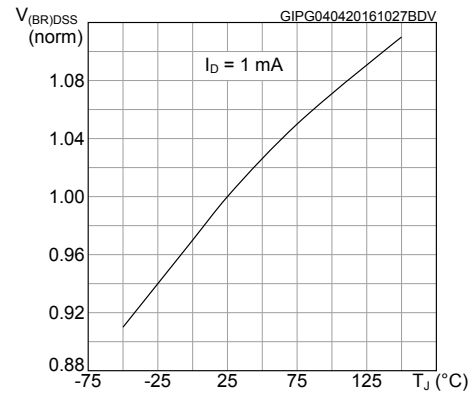
**Figure 8. Normalized gate threshold voltage vs temperature**



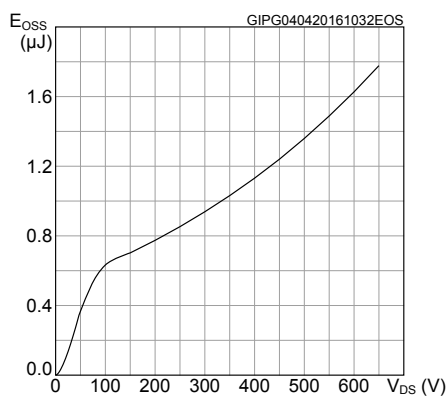
**Figure 9. Normalized on-resistance vs temperature**



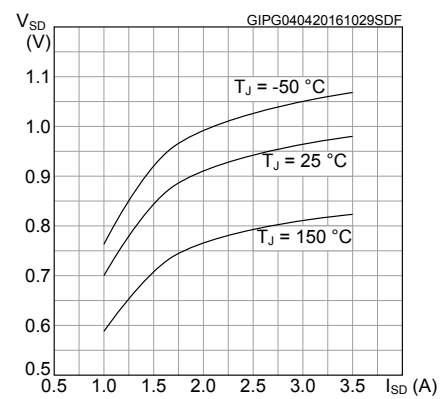
**Figure 10. Normalized V\_(BR)DSS vs temperature**



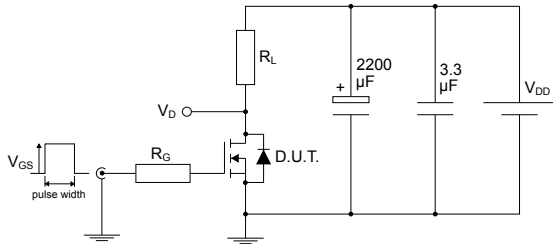
**Figure 11. Output capacitance stored energy**



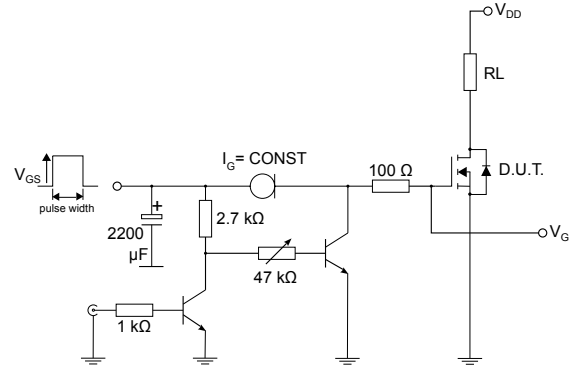
**Figure 12. Source-drain diode forward characteristics**



### 3 Test circuits

**Figure 13. Test circuit for resistive load switching times**


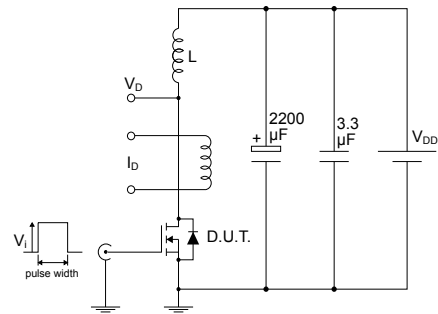
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**Figure 14. Test circuit for gate charge behavior**


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**Figure 15. Test circuit for inductive load switching and diode recovery times**


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**Figure 16. Unclamped inductive load test circuit**


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**Figure 17. Unclamped inductive waveform**


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**Figure 18. Switching time waveform**


AM01473v1

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## 4 Package information

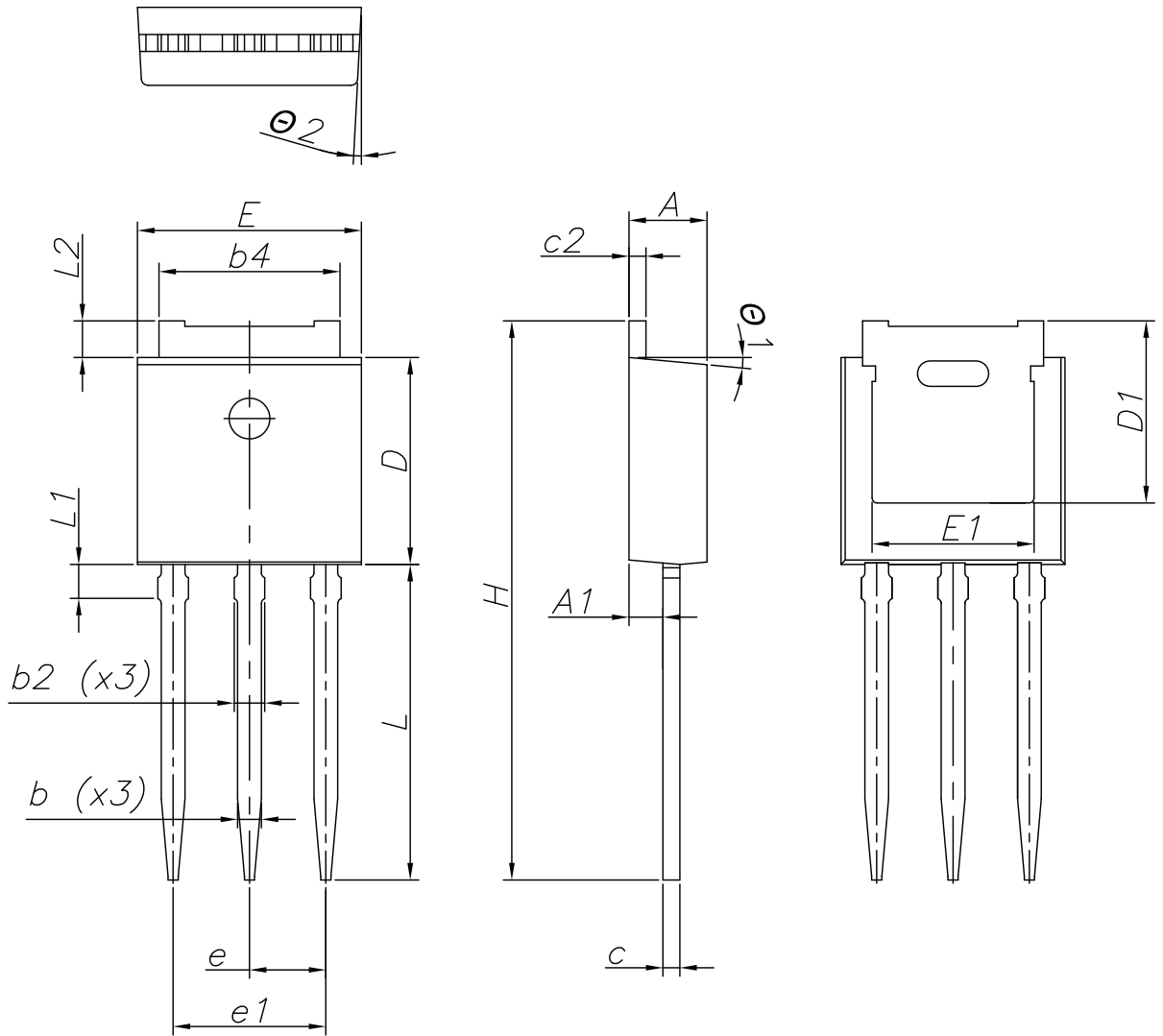
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In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.



### 4.1 IPAK (TO-251) type C package information

Figure 19. IPAK (TO-251) type C package outline



0068771\_IK\_typeC\_rev16

**Table 8. IPAK (TO-251) type C package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
02-May-2016	1	Initial release.
18-Dec-2018	2	Added <i>Section 4.2 IPAK (TO-251) type C package information.</i>
18-Jul-2023	3	Updated <i>Section 4.1 IPAK (TO-251) type C package information.</i> Minor text changes.

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